

Digital Array Radar: MPAR Applications

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Sponsored by:



Collaboration with CREE Semiconductor, Lockheed Martin, and Sierra Monolithics

Cost is a risk for the MPAR program

- Introduction
 - Trends in Electrical Engineering
 - What is a Digital Array Radar
- Current DAR Effort
 - Approach
 - GaN/ SiGE two chip channels
 - Results
- Weather-Specific Related Issues
 - Dual Polarization
- Low Cost Perspectives

To create a low cost radar it seems imperative to leverage the trends occurring at the component level.

A.) Massively Integrated RF Components, System on Chip.

-SiGe and CMOS RFIC's

B.) Widebandgap Semiconductors

-GaN and SiC – III-V semiconductors

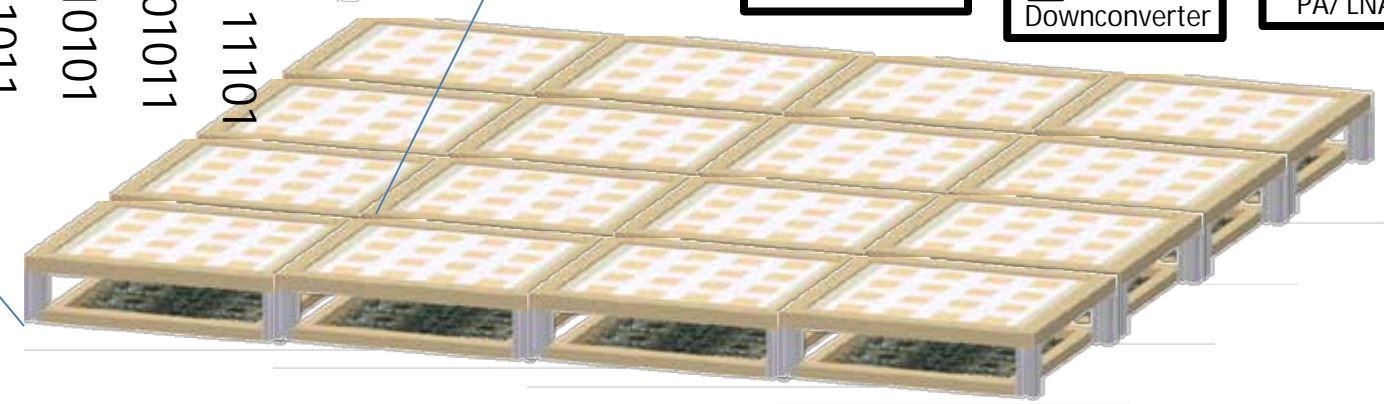
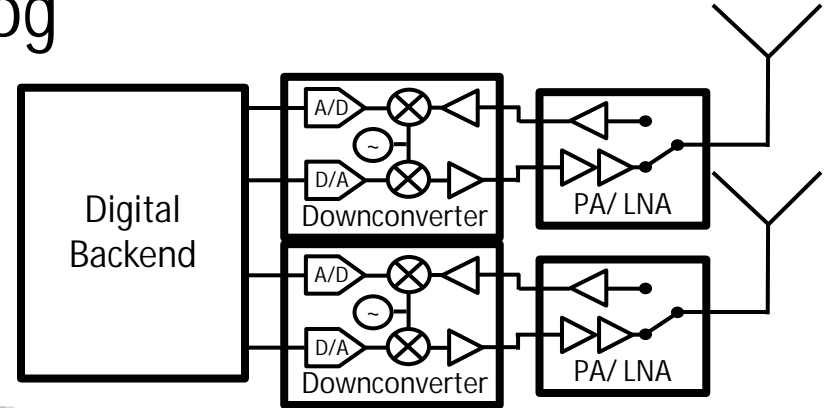
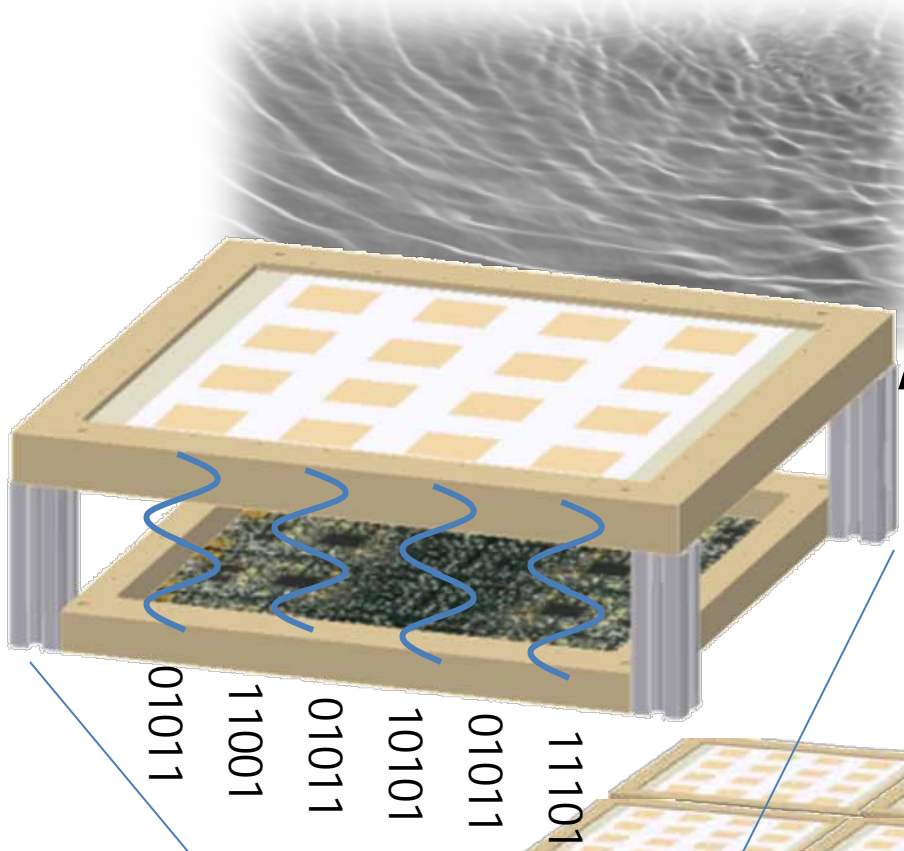
C.) Severe Impact from Digital Portion of Systems

-Calibration, adaptability, and correction by feedback from the digital domain

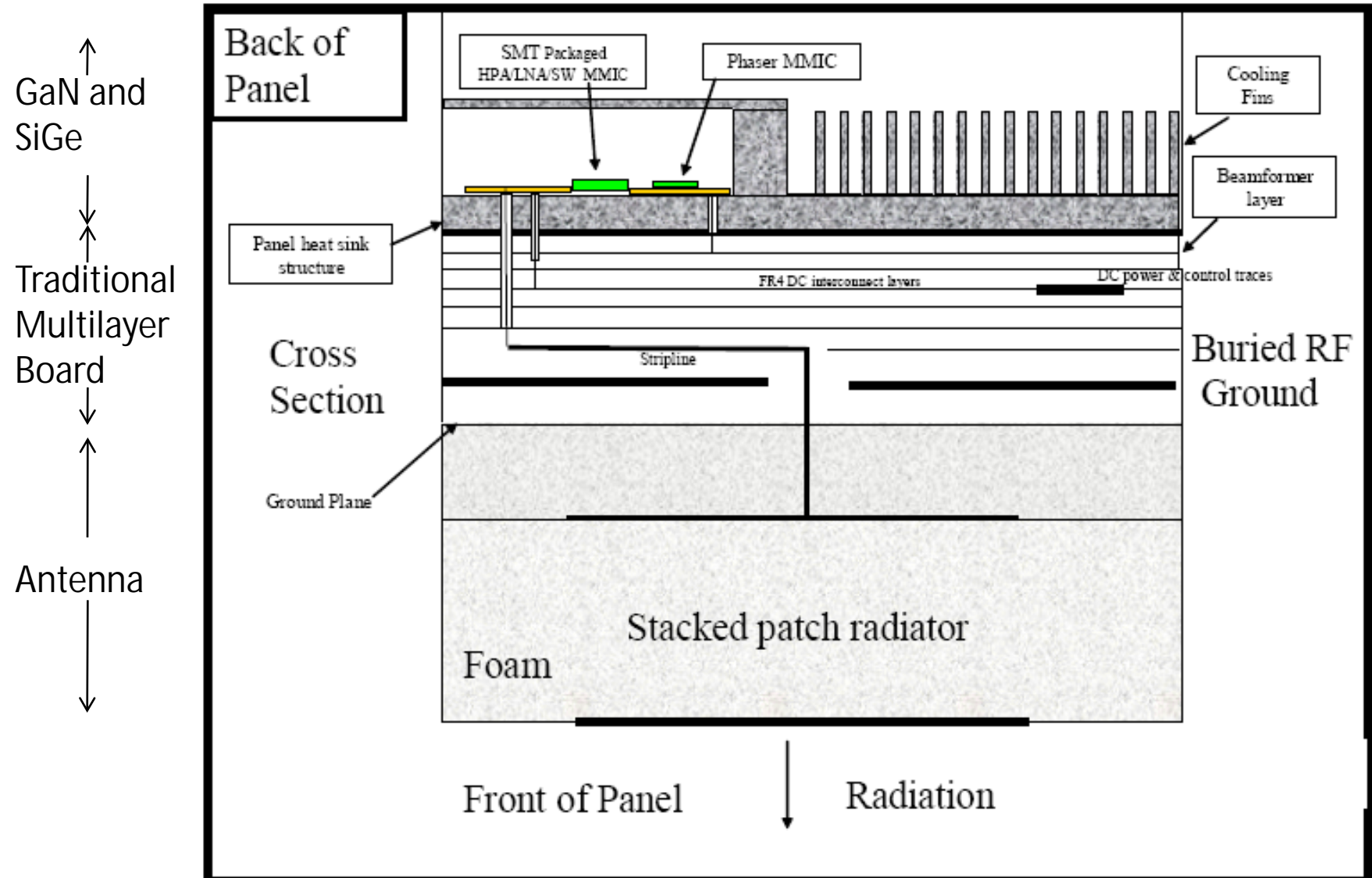
What is a Digital Array Radar?

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Digitization of the signal at each element.
The combining of signals is done in the digital domain.

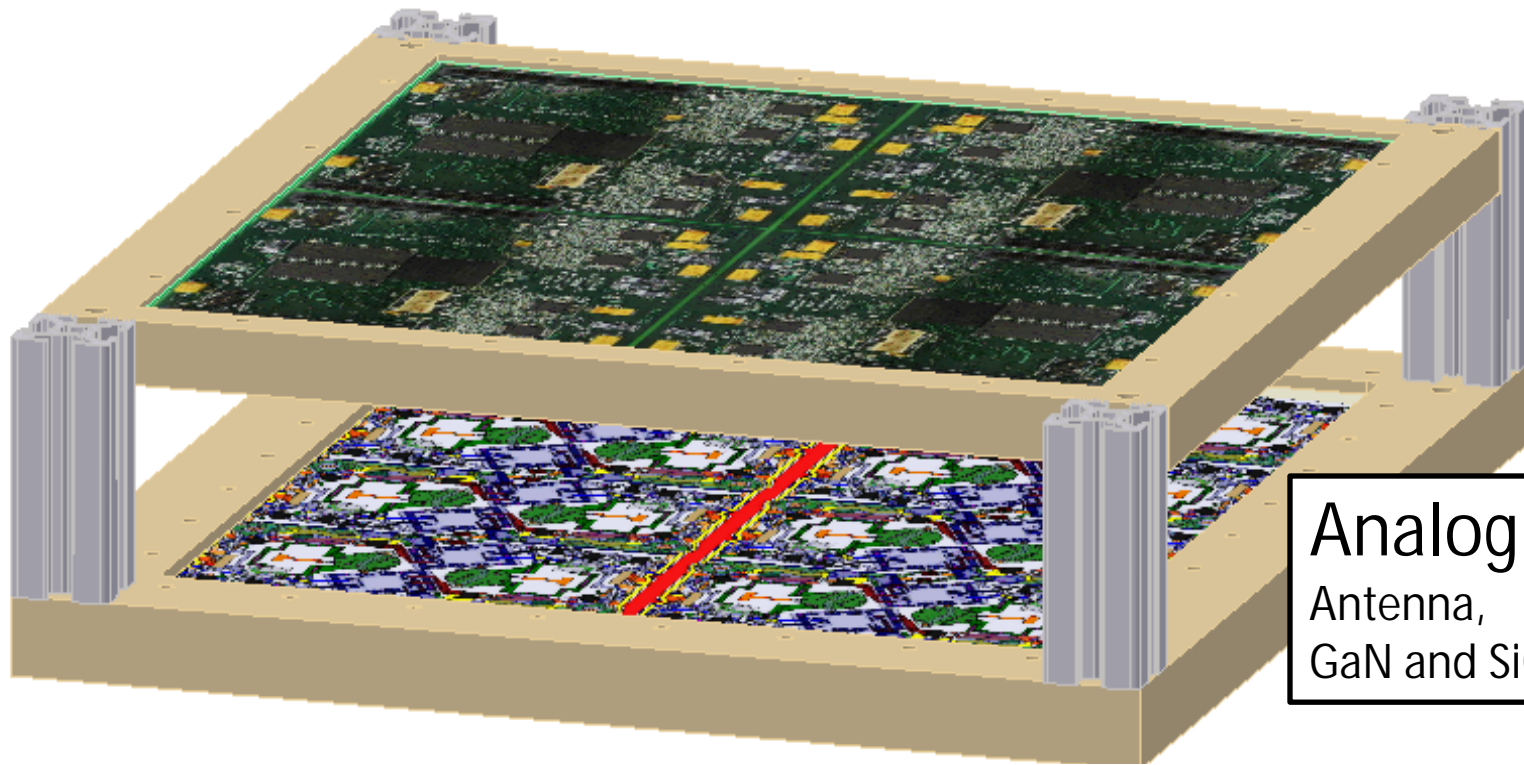


Ethernet Output

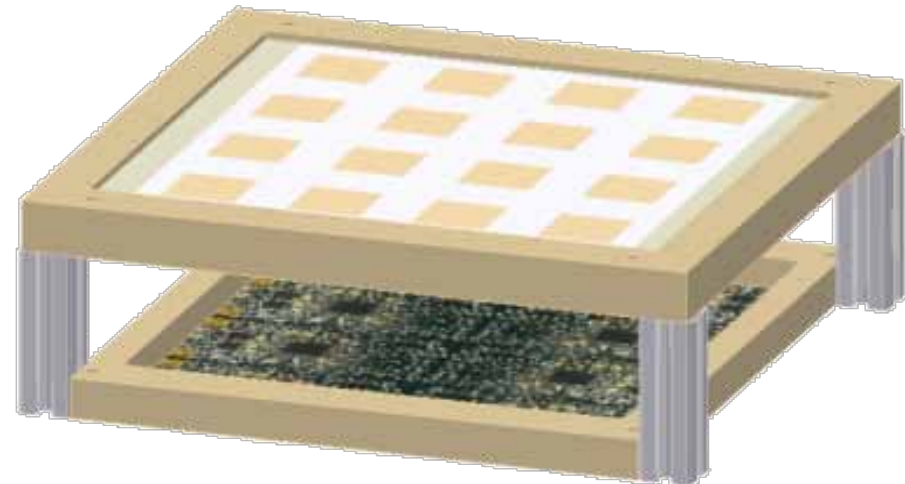


Initial Concept

DAR Program Concept V1



CAD Representations of
Final Prototype Subarray





Measured DAR Version I Prototype Subarray

On display outside for dual polarization.

A thorough overview and demo is planned at 1 PM in 1350 NWC (Next door)

Low-Cost DAR Radar

"2 Chip Radar" Solution

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Traditional Hybrid Radar Module

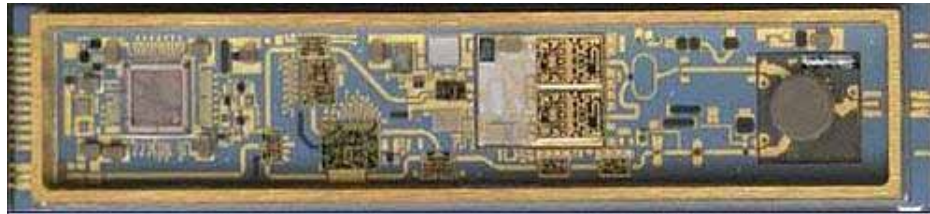
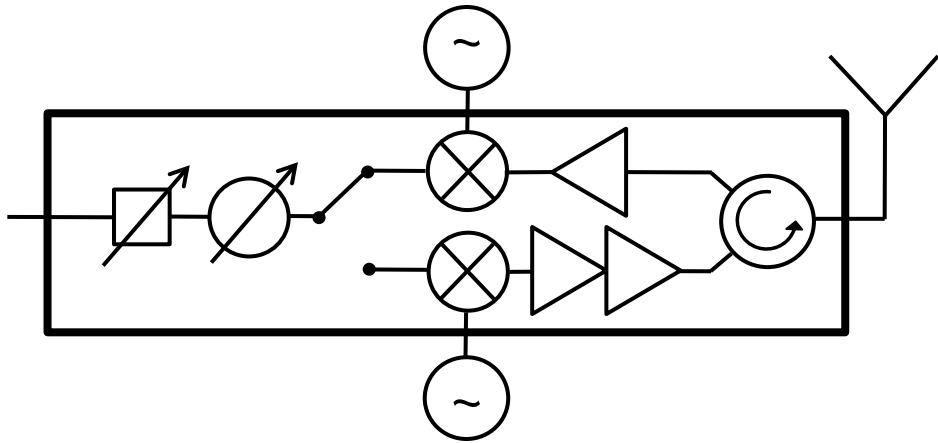
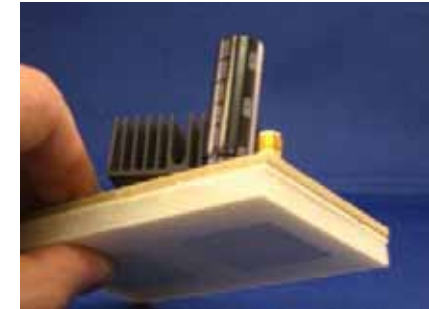
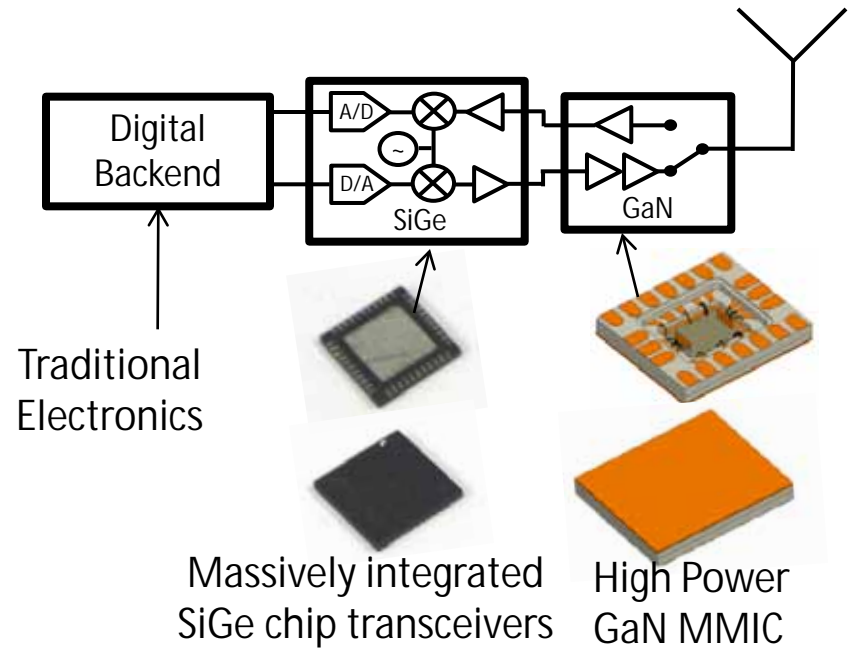


Image from Eurofighter's radar
http://www.airpower.at/news06/0922_captor-e/index.html

Advanced Integration



Planar "laptop-like" Integration – Simple 4 Layer Board for Analog Components

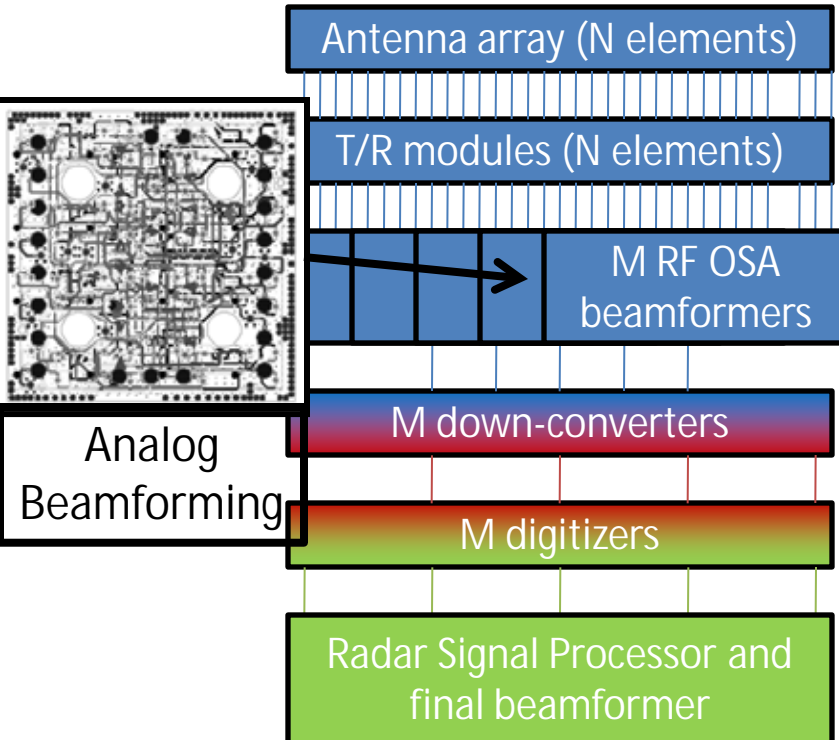
Remove Component Cost By Leveraging Commercial Integration Practices, remove T/R module
The 400 Watt Radiating "Laptop" Panel

Digital Beamforming Architectures

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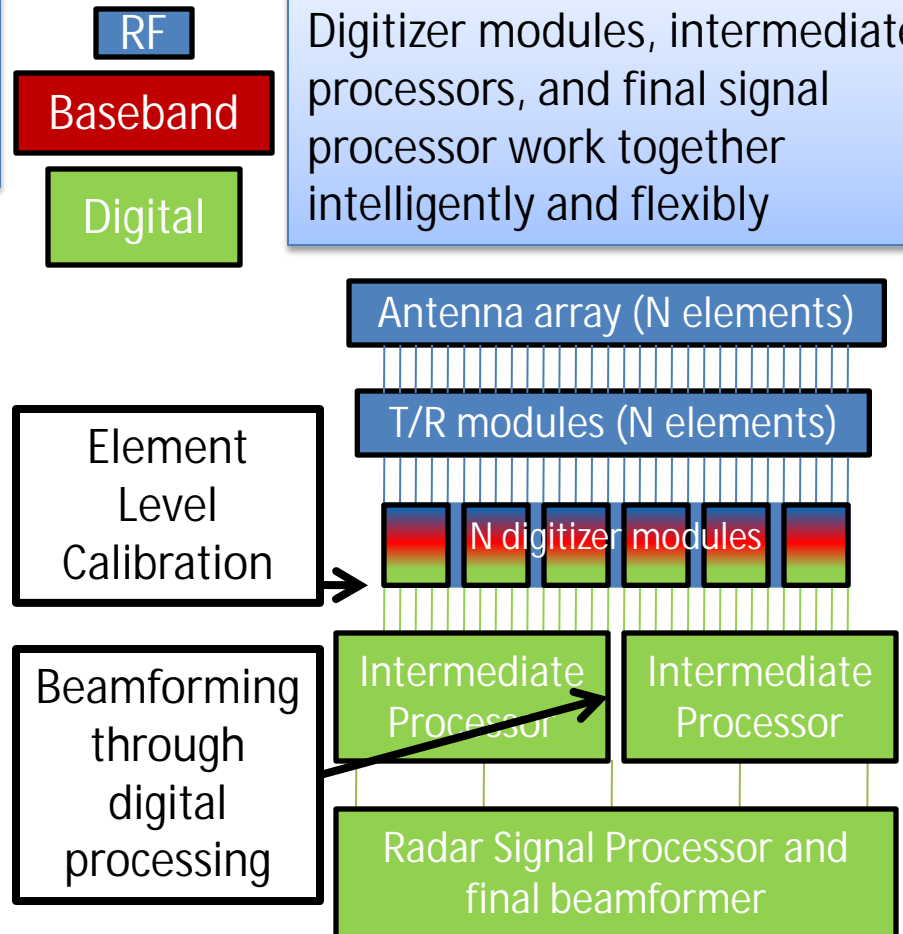
Overlapped Subarray (OSA) Digitization

Can form on the order of M simultaneous beams with purely analog beamformers



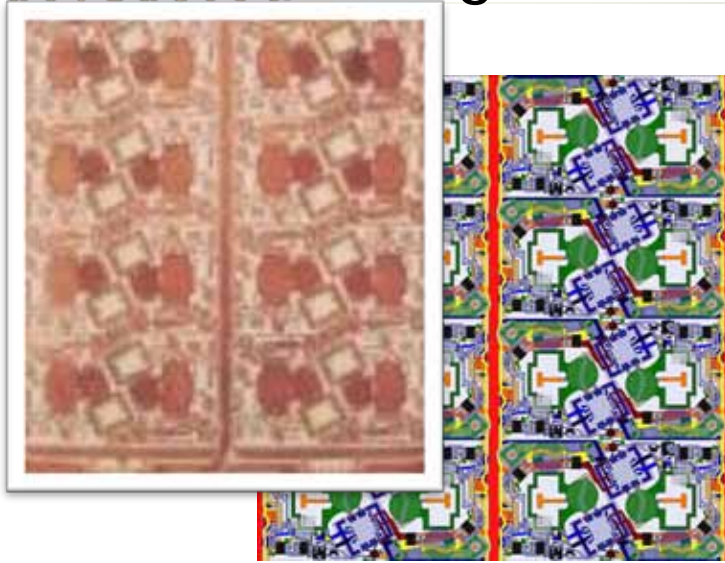
Digital at Every Element with Hierarchical Digital Backend

Digitizer modules, intermediate processors, and final signal processor work together intelligently and flexibly



High Power Plastic Antenna Array

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16 element panel

Composite multilayer polymer antenna



Large Area Integration
8x8 antenna only array constructed



- *>35 Watts per element has been demonstrated with limited cooling on RF GaN antenna panel*

- Air cooling upto 50 % duty cycle with 25 watts radiated

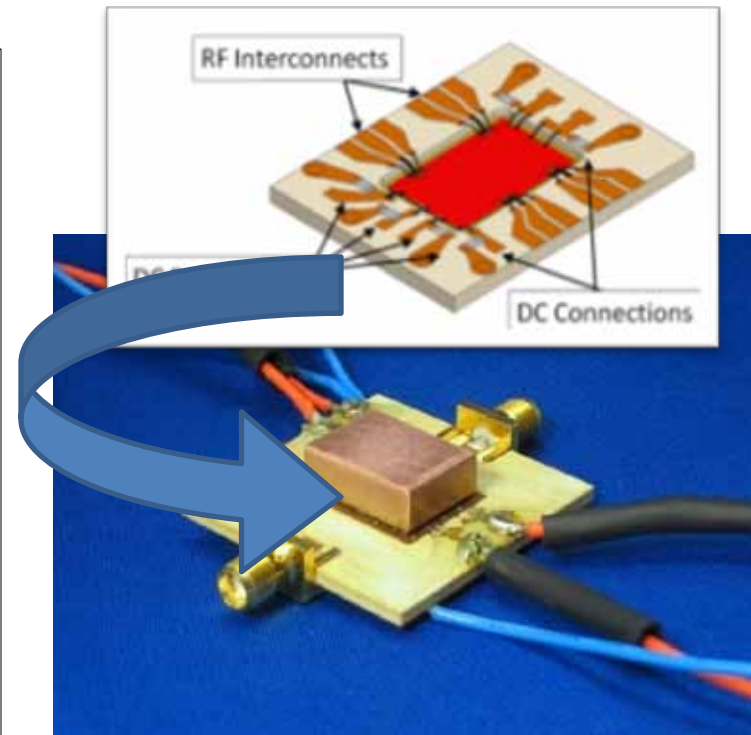
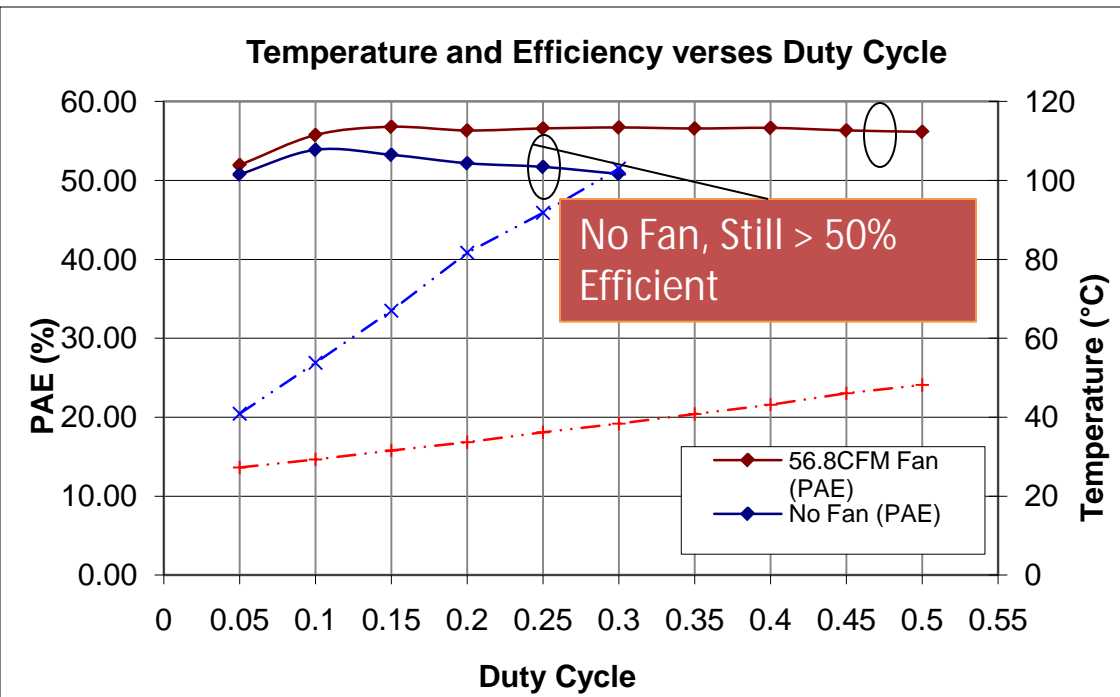
- Simulations show 80% efficiency at 7 Watts for GaN Amplifiers for 2.7 to 2.9 GHz

- Plastic QFN packages are therefore possible

Cost is Reduced Through Simplified Packaging

- Comparison of Air Cooling Techniques
- At least 10°C cooler than without a fan
- All tested points above 22dB of Gain
- Base Plate (Solid), Input Stage (Dash) and Output Stage (Dash-Dot)

Plastic Packaging and Simple Cooling Enabled through the Efficient Modes of Operation

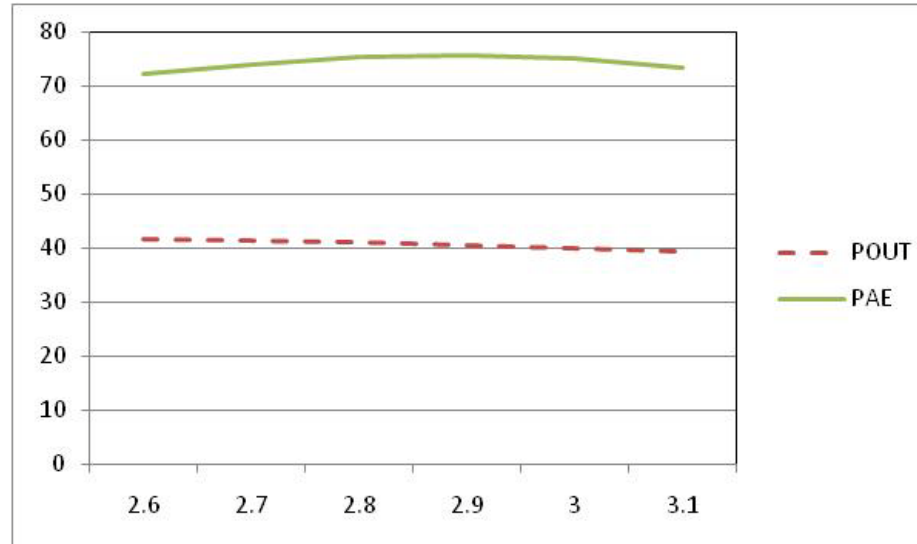


Up to 50 Watts Demonstrated in a Plastic Package

10W Ultra-High Efficiency MMIC PA

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Simulated MPAR MMIC Performance



¾ 2-Stage GaN MMIC

¾ 2 mm output stage

¾ 2.7-3.1GHz operation

¾ 50 Ohm In/Out

¾ Est. Chip Size = <4 mm²

¾ RF P_{OUT} = 10 Watts

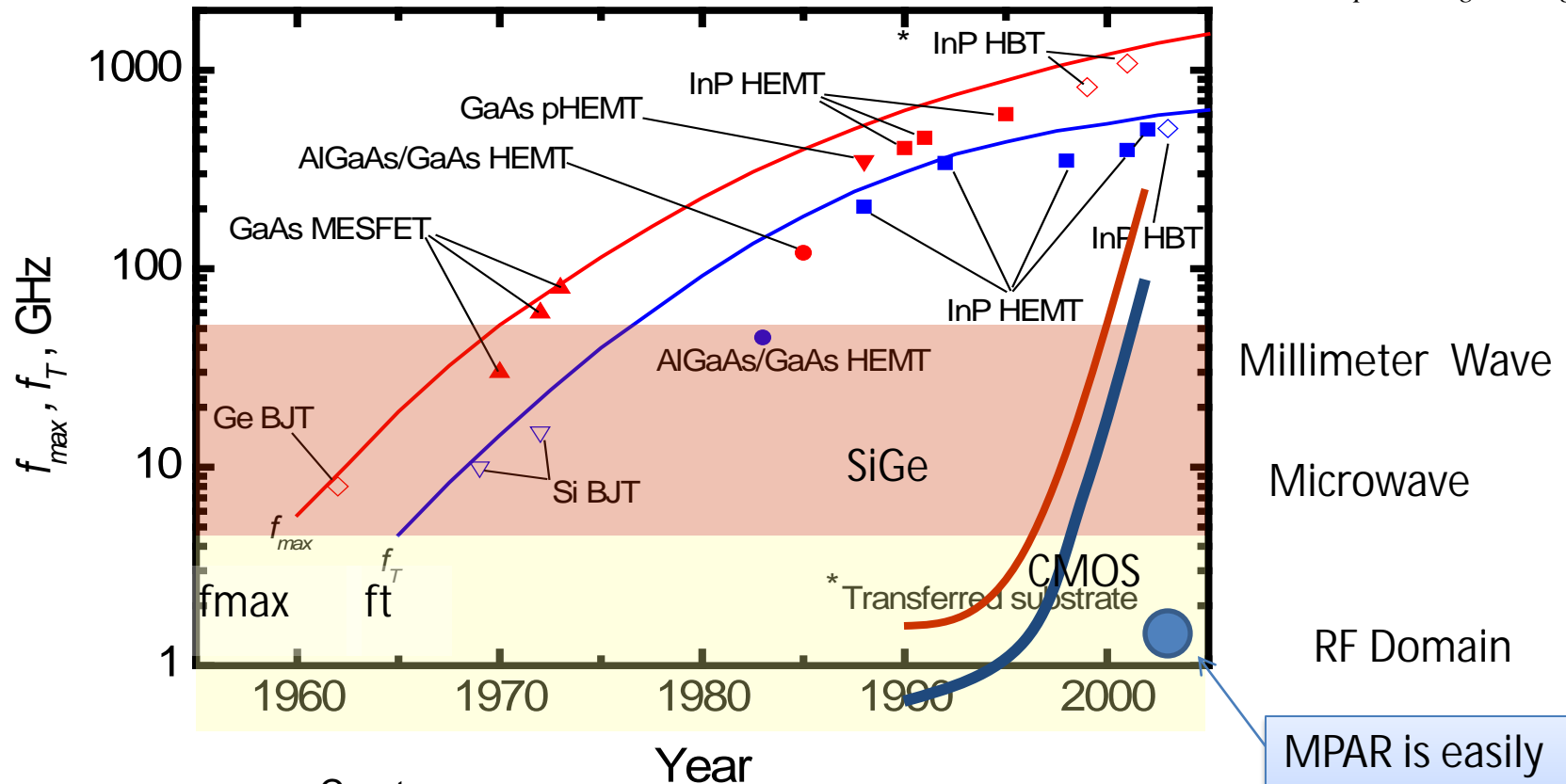
¾ PAE = 75%

¾ Large Signal Gain = 28dB

¾ Drain voltage = 28 volts

¾ Est. Production Cost: ~\$12/chip

*Cree GaN Process capable of supporting
ultra-high efficiency MPAR power amps*



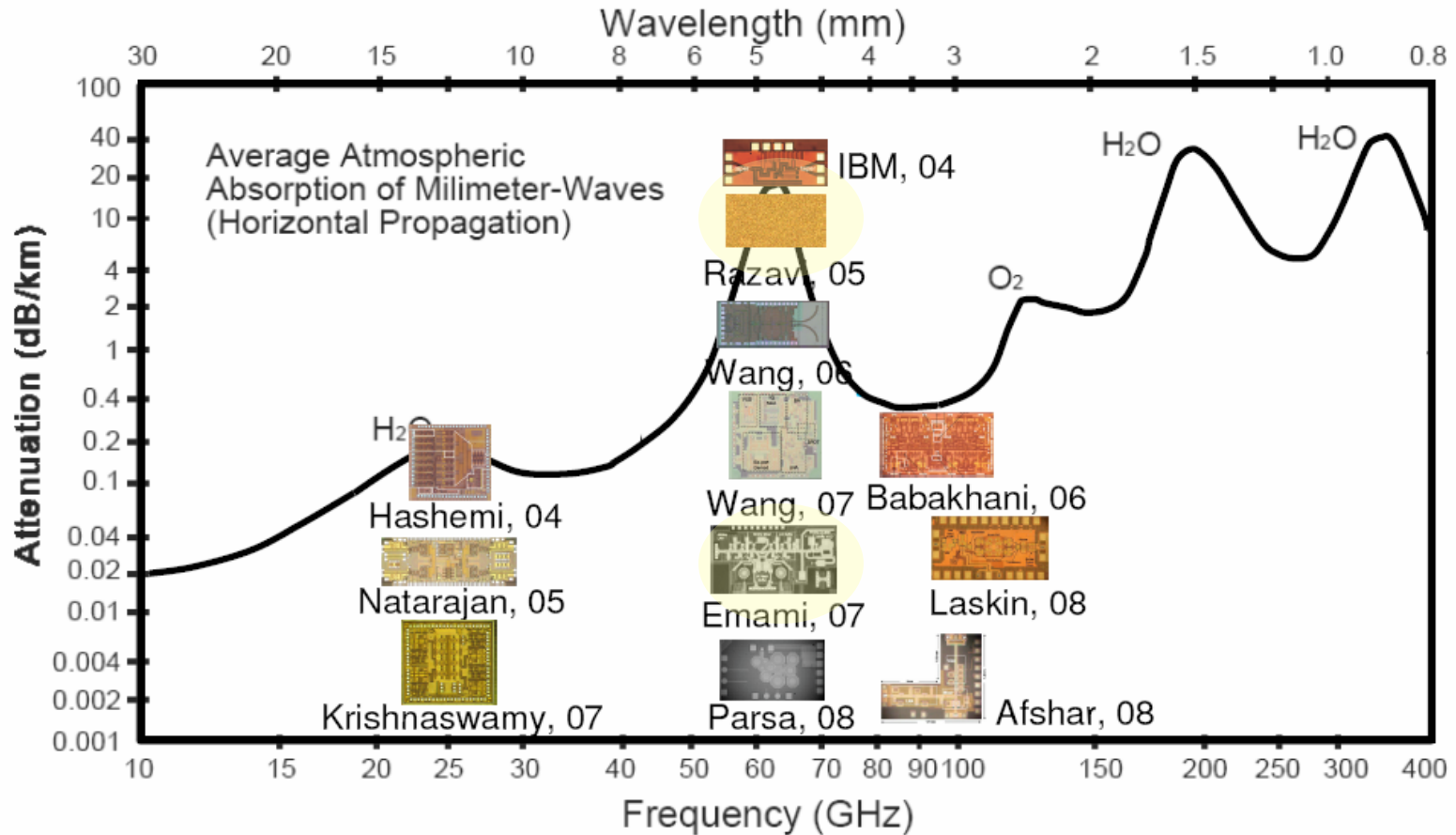
Courtesy:
www.eas.asu.edu/~vasilesk/EEE532/Talk_ASU_short.ppt

MPAR is easily within the range of silicon IC's

Important Solid State Trends:

- Continuous increase of the frequency limits, i.e. f_T and f_{max} (III-V's)
- Increase of output power (wide bandgap transistors)
- Low-cost RF transistors for consumer mass markets (Si-based)

The mm-“Wave” in Industry and Academia

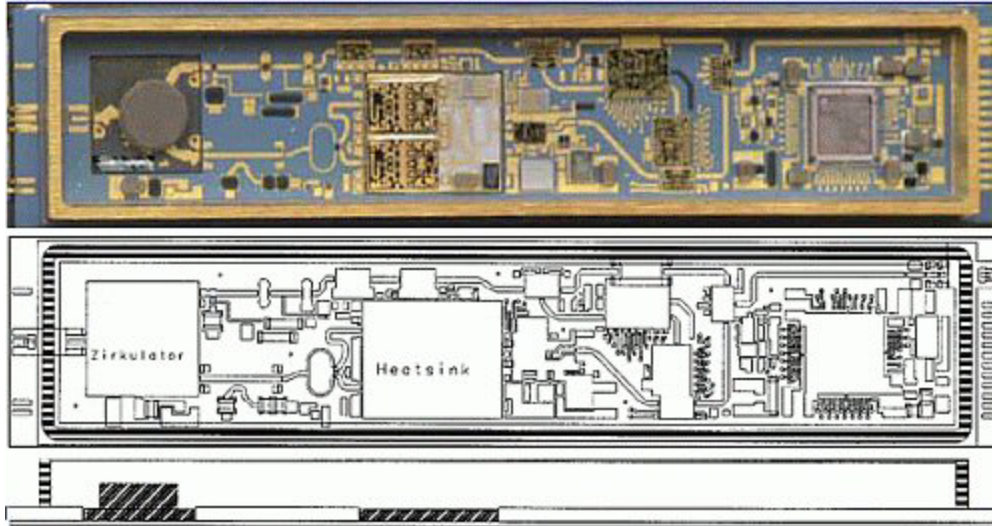


Fully-integrated mm-wave transceivers reported at ISSCC.

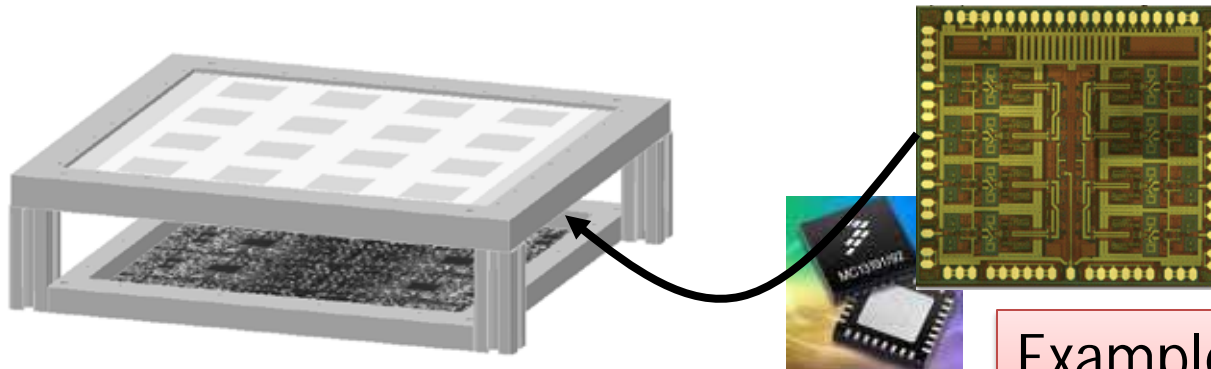
Promise of the Technology

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- Recent Demonstrations – 8 element receive only array that is 2 by 3 mm in Jazz .18 micron SiGe – Works from 6 to 18 GHz (UCSD)



Multichip Module
Replaced by
Multireceiver Silicon IC



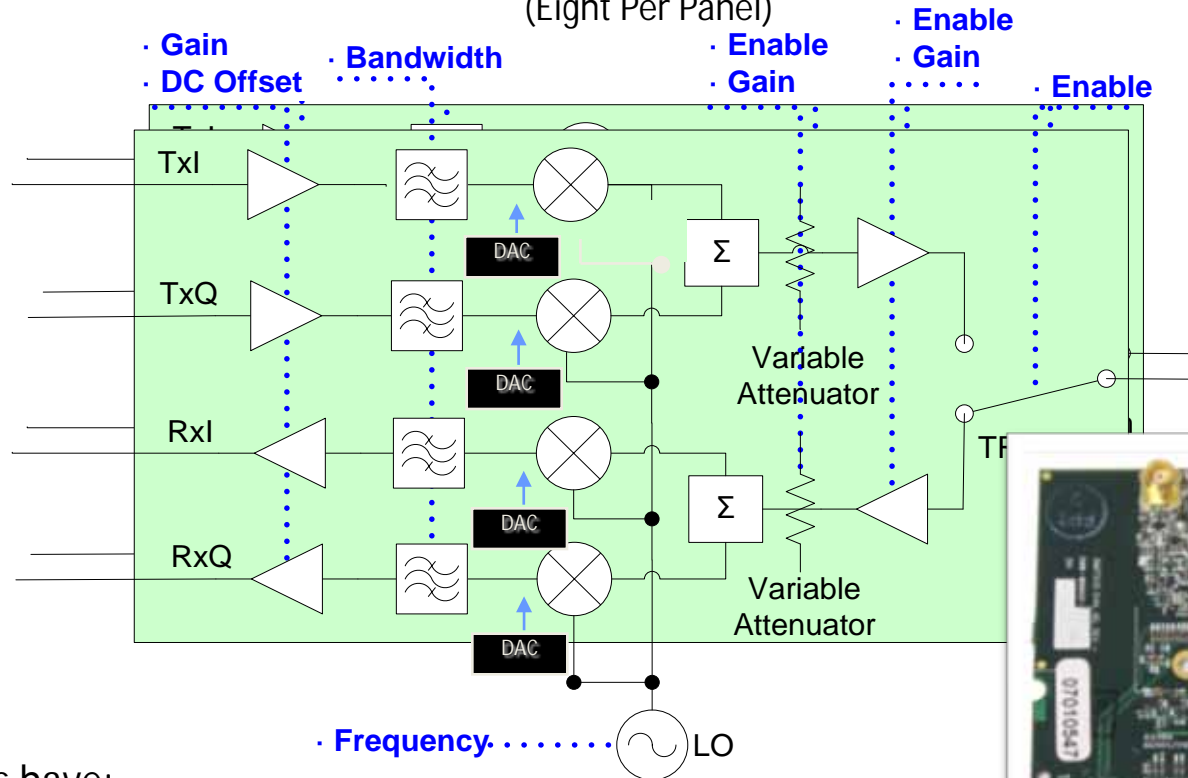
Example of 16
elements on a chip

“motherboard-like RF array integration”

SiGe integration allows for more than 1 radar channel per chip. Beyond (SOC) System on Chip



Sierra Monolithics (SMI) 2x2 WiMAX Transceiver
(Eight Per Panel)

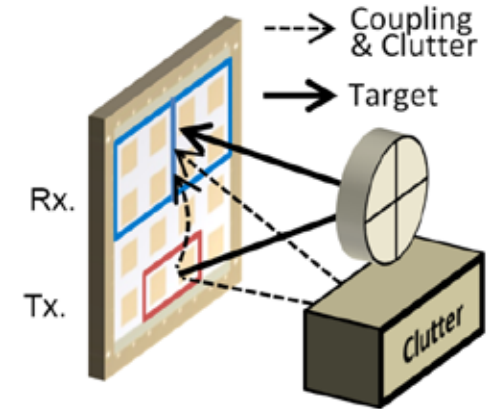
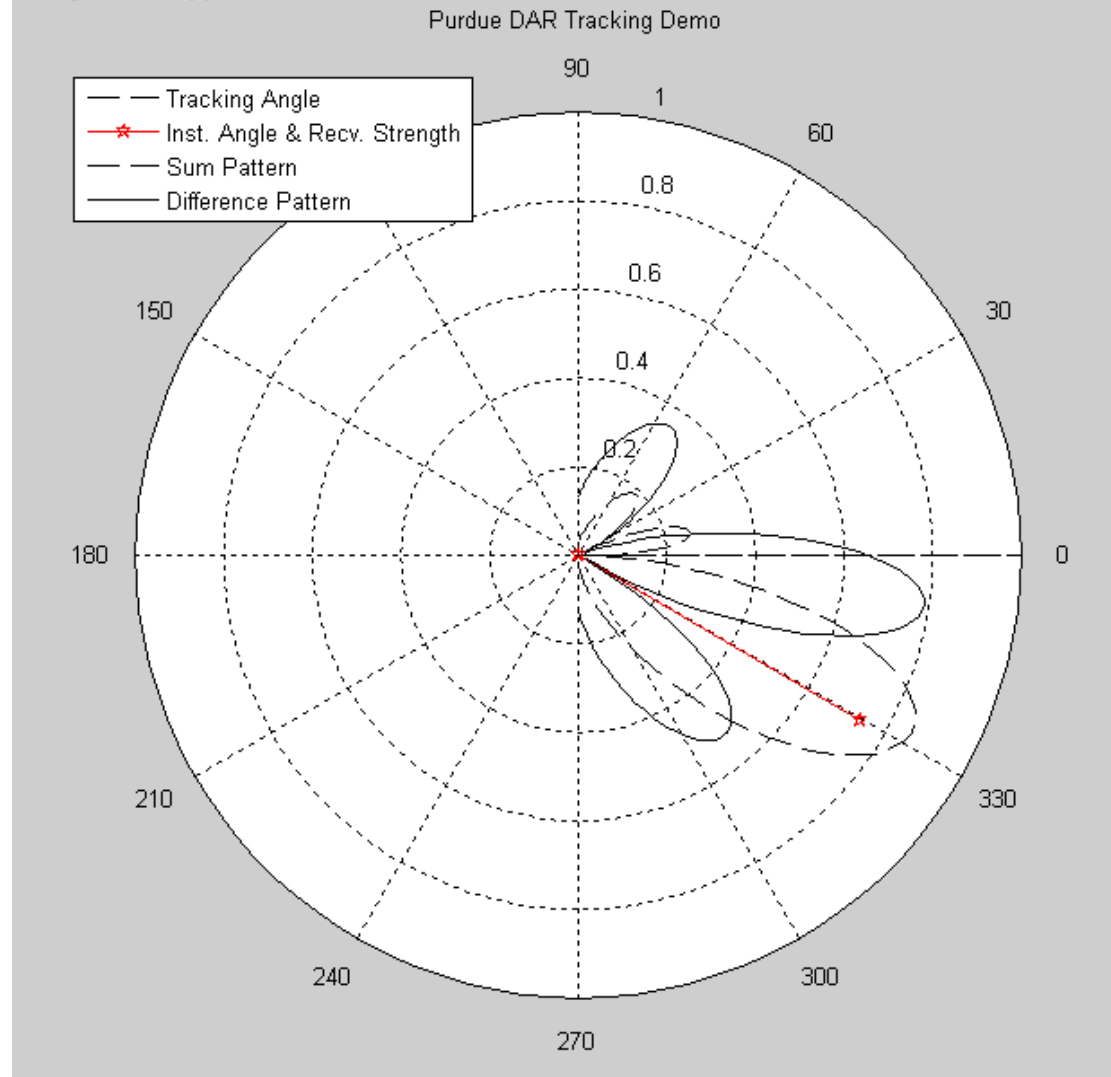


- SMI boards have:
 - Two independent direct-conversion I/Q Tx/Rx channels per board
 - 54 programmable registers
 - Flexibility in gain, filtering, DC offset compensation, etc.
 - Programmable RF LOs on each board

Tracking Demonstration

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Unregistered HyperCam 2



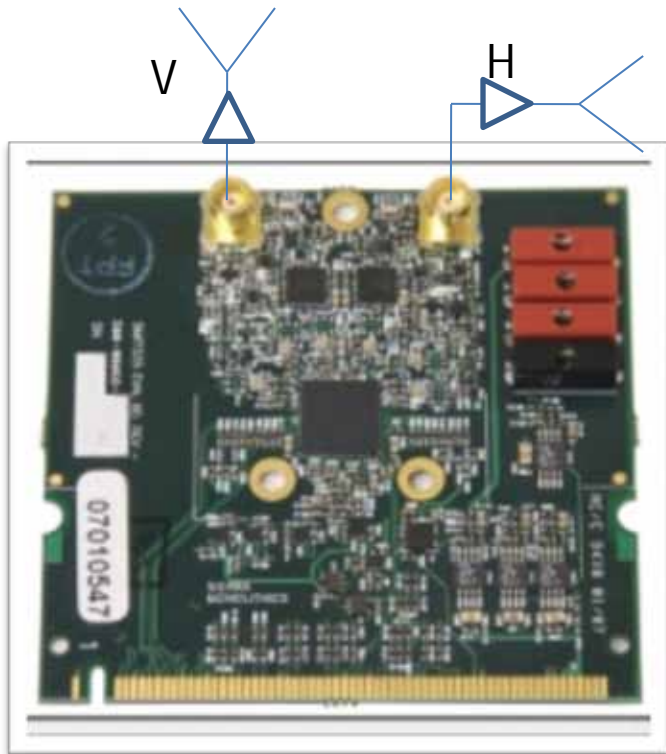
Tracking demonstrated using digital beamformer

Dual Polarization Variation of DAR

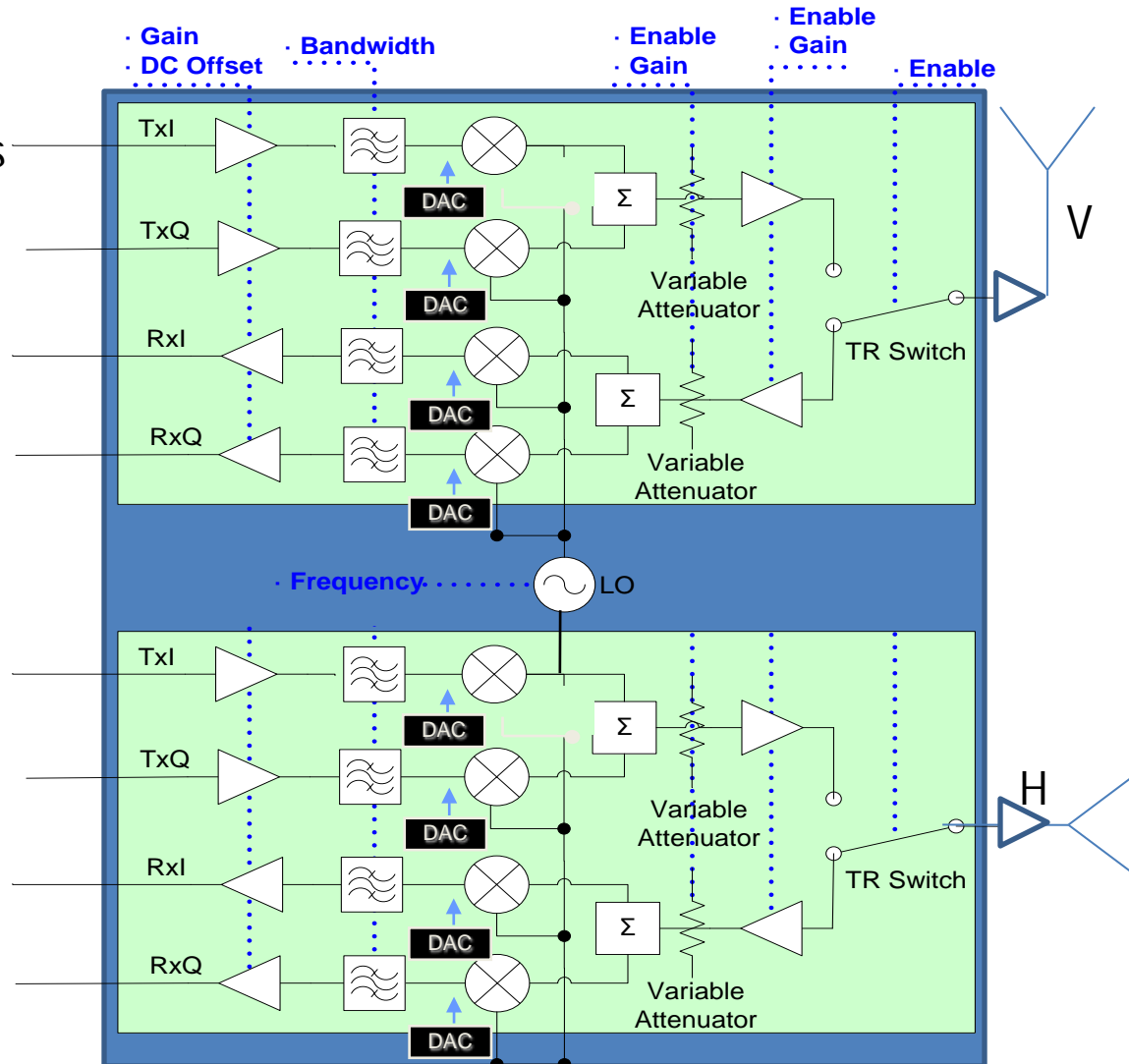
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The integrated SiGe transceiver is very useful for dual polarization

There are two channels on one integrated circuit, so one IC handles both inputs from the antennas.



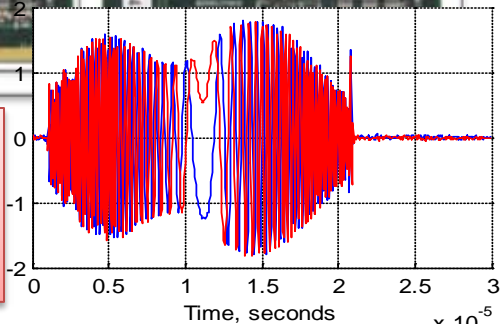
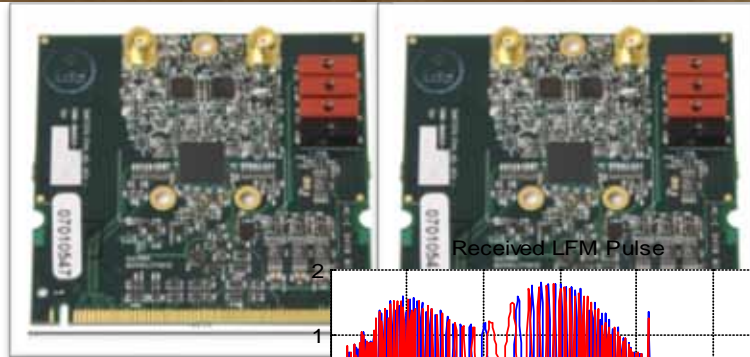
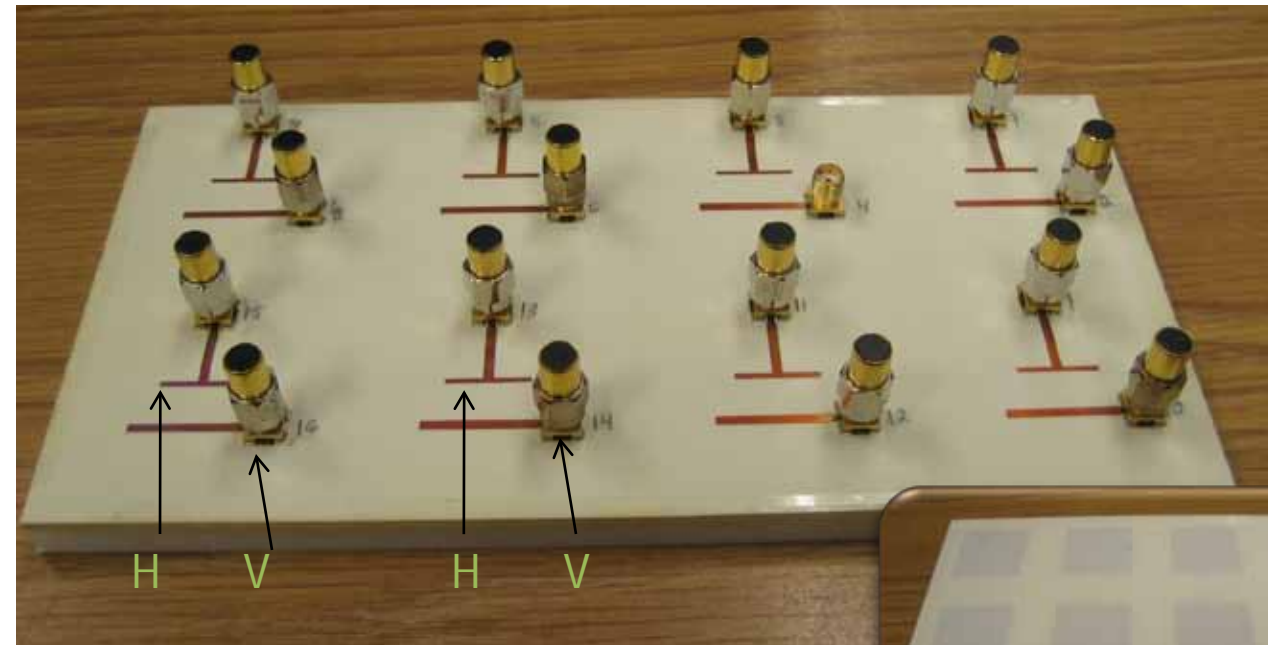
Direct Data Output



DAR Dual Polarization Work

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-40 dB isolation between polarizations



Measured V and H data of LFM pulse

Measured simultaneous transmit on each polarization

Independent waveform synthesis at each antenna will allow for compensation of polarization mismatches to improve polarization metrics

- Cost is a risk for the MPAR program

- Leveraging the advances at the component level will be useful for pushing the cost curve down

- Massive Integration - SiGe

- High Power Plastic Operation – GaN

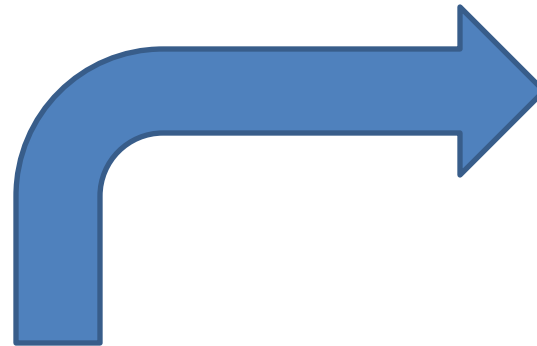
- Digital Utilization – Digital at Every Element

- Let the broader electronics world do the heavy lifting

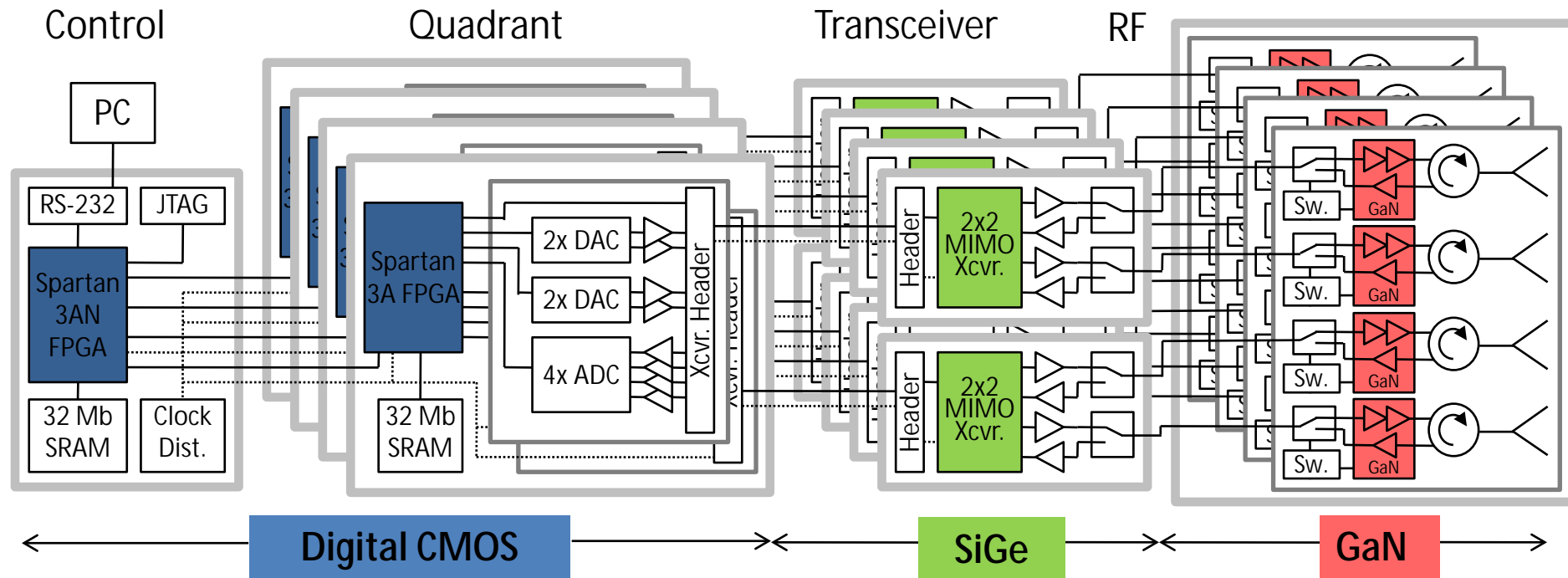
Digital at every element has been demonstrated for a 16 element panel.

A low cost phased array can be built if commercial trends and practices are leveraged.

A detailed overview of the array and a demonstration of the performance will be shown at 1 PM in room



Next door, 1 PM



5) Synchronization
Digital backend Control board designed, laid out, and populated in-house

Wrote firmware for FPGAs and software for host PC interface

3) Silicon Integration Utilized integrated Sierra Monolithics 2x2 WiMAX SiGe transceiver

1) Antenna Panelization Antenna was designed, analyzed for mutual coupling, fabricated, and tested

4) Digital Processing Quadrant boards perform data conversion and element-level processing

2) Plastic High Power Packaging Multi-layer panel and plastic packaging designed to house efficient GaN T/R modules